



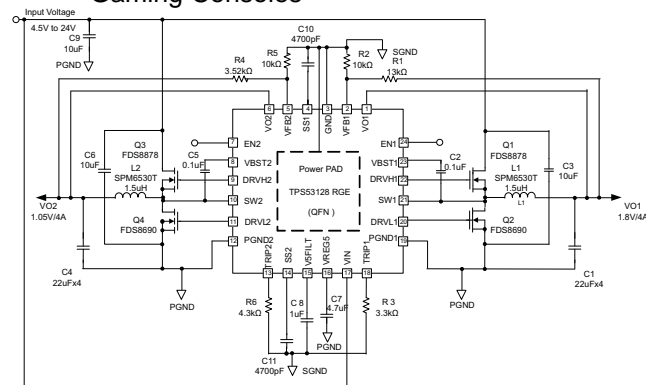
# TPS53128 Dual Synchronous Step-Down Controller With Auto-SkipEco-mode™ For Low Voltage Power Rails

## 1 Features

- D-CAP2™ Mode Control
  - Fast Transient Response
  - No External Parts Required for Loop Compensation
  - Compatible With Ceramic Output Capacitors
- High Initial Reference Accuracy ( $\pm 1\%$ )
- Low Output Ripple
- Wide Input Voltage Range: 4.5 V to 24 V
- Output Voltage Range: 0.76 V to 5.5 V
- Low-Side  $R_{DS(ON)}$  Loss-Less Current Sensing
- Adaptive Gate Drivers with Integrated Boost Diode
- Adjustable Soft Start
- Non-Sinking Pre-Biased Soft Start
- 350-kHz Switching Frequency
- Cycle-by-Cycle Over-Current Limiting Control
- 30-mV to 300-mV OCP Threshold Voltage
- Thermally Compensated OCP by 4000 ppm/°C at  $I_{TRIP}$
- Auto-Skip Eco-mode™ for High Efficiency at Light Load

## 2 Applications

- Point-of-Load Regulation in Low Power Systems for Wide Range of Applications
  - Digital TV Power Supply
  - Networking Home Terminal
  - Digital Set-Top Box (STB)
  - DVD Player/Recorder
  - Gaming Consoles



## 3 Description

The TPS53128 is a dual, adaptive on-time D-CAP2™ mode synchronous buck controller. The part enables system designers to cost effectively complete the suite of various end equipment's power bus regulators with a low external component count and low standby consumption. The main control loop for the TPS53128 uses the D-CAP2™ Mode topology which provides a very fast transient response with no external component.

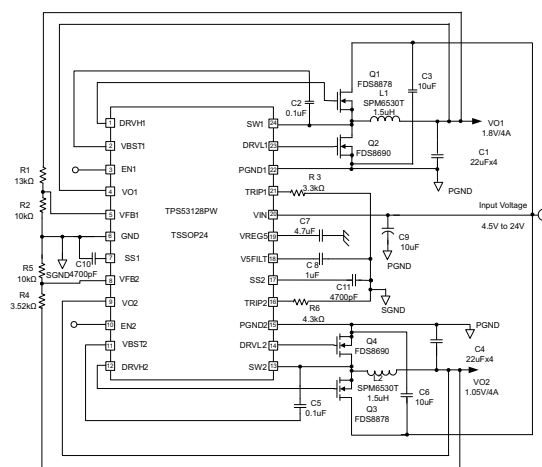
The TPS53128 also has a proprietary circuit that enables the device to adapt not only low equivalent series resistance (ESR) output capacitors such as POSCAP/SP-CAP, but also ceramic capacitor. The fixed frequency emulated adaptive on-time control supports seamless operation between PWM mode at heavy load condition and reduced frequency operation at light load for high efficiency down to milliampere range. The part provides a convenient and efficient operation with conversion voltages from 4.5 V to 24 V and output voltage from 0.76 V to 5.5 V.

The TPS53128 is available in 4-mm x 4-mm 24 pin QFN (RGE) or 24 pin TSSOP (PW) packages, and is specified from -40°C to 85°C ambient temperature range.

**Table 1. Device Information<sup>(1)</sup>**

DEVICE NAME	PACKAGE	BODY SIZE
TPS53128	VQFN (24)	4.4 mm x 7.8 mm
	TSSOP (24)	4 mm x 4 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.



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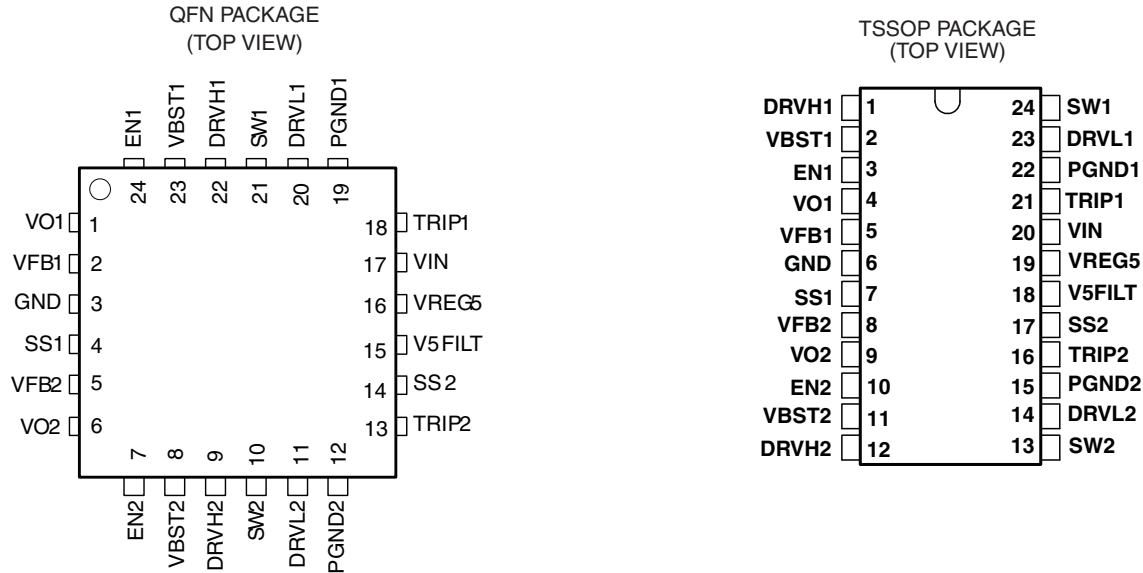
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<b>2 Applications</b> .....	<b>1</b>	7.4 Device Functional Modes.....	<b>14</b>
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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Original (July 2010) to Revision A</b>	<b>Page</b>
• Changed format to meet latest data sheet standards; added new sections and moved existing sections.....	<b>1</b>
• Added Eco-mode bullet to <a href="#">Features</a> .....	<b>1</b>
• Added QFN and TSSOP schematics .....	<b>1</b>
• Added $V_{(ESD)}$ value .....	<b>4</b>
• Added thermal information .....	<b>5</b>
• Changed min for $V_{VREG5}$ .....	<b>5</b>
• Changed max for $R_{DRV1}$ at -100 mA .....	<b>5</b>
• Changed the $I(SSC)$ Min value From: -1.5 to -2.5 $\mu A$ and the Max value From: -2.5 To: -1.5 $\mu A$ .....	<b>6</b>
• Added Overview section. ....	<b>10</b>
• Added Device Functional Modes .....	<b>14</b>
• Added Design Parameter values .....	<b>16</b>
• Added Power Supply Recommendations .....	<b>23</b>
• Added Layout Example image.....	<b>24</b>

## 5 Pin Configuration and Functions



**Table 2. Pin Functions**

PIN			I/O	DESCRIPTION
NAME	RGE	PW		
VBST1, VBST2	23, 8	2, 11	I	Supply input for high-side NFET driver. Bypass to SWx with a high-quality 0.1-μF ceramic capacitor. An external schottky diode can be added from VREG5 if forward drop is critical to drive the high-side FET.
EN1, EN2	24, 7	3, 10	I	Enable. Pull High to enable SMPS.
VO1, VO2	1, 6	4, 9	I	Output voltage inputs for on-time adjustment and output discharge. Connect directly to the output voltage.
VFB1, VFB2	2, 5	5, 8	I	D-CAP2 feedback inputs. Connect to output voltage with resistor divider.
GND	3	6	I	Signal ground pin. Connect to PGND1, PGND2 and system ground at a single point.
DRVH1, DRVH2	22, 9	1, 12	O	High-side N-Channel MOSFET gate driver outputs. SWx referenced drivers switch between SWx (OFF) and VBSTx (ON).
SW1, SW2	21, 10	24, 13	I/O	Switch node connections for both the high-side drivers and the over current comparators.
DRVL1, DRVL2	20, 11	23, 14	O	Low-side N-Channel MOSFET gate driver outputs. PGND referenced drivers switch between PGNDx (OFF) and VREG5 (ON).
PGND1, PGND2	19, 12	22, 15	I/O	Power ground connections for both the low-side drivers and the over current comparators. Connect PGND1, PGND2 and GND strongly together near the IC.
TRIP1, TRIP2	18, 13	21, 16	I	Over current threshold programming pin. Connect to GND with a resistor to GND to set threshold for low-side $R_{DS(ON)}$ current limit.
VIN	17	20	I	Supply Input for 5-V linear regulator. Bypass to GND with a minimum high-quality 0.1-μF ceramic capacitor.
V5FILT	15	18	I	5-V supply input for the entire control circuitry except the MOSFET drivers. Bypass to GND with a minimum high-quality 1.0-μF ceramic capacitor. V5FILT is connected to VREG5 via an internal 10-Ω resistor.
VREG5	16	19	O	Output of 5-V linear regulator and supply for MOSFET drivers. Bypass to GND with a minimum high-quality 4.7-μF ceramic capacitor. VREG5 is connected to V5FILT via an internal 10-Ω resistor.
SS1, SS2	4, 14	7, 17	O	Soft-start programming pin. Connect capacitor from SSx pin to GND to program soft-start time.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

		VALUE	UNIT
$V_I$	Input voltage	VIN, EN1, EN2	–0.3 to 26
		VBST1, VBST2	–0.3 to 32
		VBST1 - SW1, VBST2 - SW2	–0.3 to 6
		V5FILT, VFB1, VFB2, TRIP1, TRIP2, VO1, VO2	–0.3 to 6
		SW1, SW2	–2 to 26
$V_O$	Output voltage	DRVH1, DRVH2	–1 to 32
		DRVH1 - SW1, DRVH2 - SW2	–0.3 to 6
		DRVL1, DRVL2, VREG5, SS1, SS2	–0.3 to 6
		PGND1, PGND2	–0.3 to 0.3
$T_A$	Operating ambient temperature	–40 to 85	°C
$T_J$	Junction temperature	–40 to 150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" are not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 Handling Ratings

			MIN	MAX	UNIT
$T_{stg}$	Storage temperature range		–55	150	°C
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AN/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	–2000	2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	–500	500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
$V_{IN}$	Supply input voltage	VIN	4.5	24	V
		V5FILT	4.5	5.5	
$V_I$	Input voltage	VBST1, VBST2	–0.1	30	V
		VBST1 - SW1, VBST2 - SW2	–0.1	5.5	
		VFB1, VFB2, VO1, VO2	–0.1	5.5	
		TRIP1, TRIP2	–0.1	0.3	
		EN1, EN2	–0.1	24	
		SW1, SW2	–1.8	24	
$V_O$	Output voltage	DRVH1, DRVH2	–0.1	30	V
		VBST1 - SW1, VBST2 - SW2	–0.1	5.5	
		DRVL1, DRVL2, VREG5, SS1, SS2	–0.1	5.5	
		PGND1, PGND2	–0.1	0.1	
$T_A$	Operating free-air temperature		–40	85	°C
$T_J$	Operating junction temperature		–40	125	°C

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS53128		UNIT
		RGE	PW	
		24 PIN	24PIN	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	35.4	88.9	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	39.1	26.5	
R <sub>θJB</sub>	Junction-to-board thermal resistance	13.6	43.5	
ψ <sub>JT</sub>	Junction-to-top characterization parameter	0.5	1.1	
ψ <sub>JB</sub>	Junction-to-board characterization parameter	13.6	43	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	3.8	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
I <sub>IN</sub>	VIN supply current	VIN current, T <sub>A</sub> = 25°C, VREG5 tied to V5FILT, EN1 = EN2 = 5 V, VFB1 = VFB2 = 0.8 V, SW1 = SW2 = 0.5 V		450	800	μA
I <sub>VINSDN</sub>	VIN shutdown current	VIN current, T <sub>A</sub> = 25°C, no load , EN1 = EN2 = 0 V, VREG5 = ON		30	60	μA
VFB VOLTAGE AND DISCHARGE RESISTANCE						
V <sub>BG</sub>	Bandgap initial regulation accuracy	T <sub>A</sub> = 25°C	–1		1	%
V <sub>VFBTHx</sub>	VFBx threshold voltage	T <sub>A</sub> = 25°C, SW <sub>inj</sub> = OFF	755	765	775	mV
		TA = 0°C to 70°C, SW <sub>inj</sub> = OFF <sup>(1)</sup>	753.5		776.5	
		T <sub>A</sub> = -40°C to 85°C, SW <sub>inj</sub> = OFF <sup>(1)</sup>	752		778	
I <sub>VFB</sub>	VFB input current	VFBx = 0.8 V, T <sub>A</sub> = 25°C	–100	–10	100	nA
R <sub>Dischg</sub>	VO discharge resistance	ENx = 0 V, VOx = 0.5 V, T <sub>A</sub> = 25°C		40	80	Ω
VREG5 OUTPUT						
V <sub>VREG5</sub>	VREG5 output voltage	T <sub>A</sub> = 25°C, 5.5 V < VIN < 24 V, 0 < I <sub>VREG5</sub> < 10 mA	4.6	5.0	5.2	V
V <sub>LN5</sub>	Line regulation	5.5 V < VIN < 24 V, I <sub>VREG5</sub> = 10 mA			20	mV
V <sub>LD5</sub>	Load regulation	1 mA < I <sub>VREG5</sub> < 10 mA			40	mV
I <sub>VREG5</sub>	Output current	VIN = 5.5 V, V <sub>VREG5</sub> = 4.0 V, T <sub>A</sub> = 25°C		170		mA
OUTPUT: N-CHANNEL MOSFET GATE DRIVERS						
R <sub>DRVH</sub>	DRVH resistance	Source, I <sub>DRVHx</sub> = –100 mA		5.5	11	Ω
		Sink, I <sub>DRVHx</sub> = 100 mA		2.5	5	
R <sub>DRVL</sub>	DRVL resistance	Source, I <sub>DRVLx</sub> = –100 mA		4	12	Ω
		Sink, I <sub>DRVLx</sub> = 100 mA		2	4	
T <sub>D</sub>	Dead time	DRVHx-low to DRVLx-on	20	50	80	ns
		DRVLx-low to DRVHx-on	20	40	80	
INTERNAL BOOST DIODE						
V <sub>FBST</sub>	Forward voltage	V <sub>VREG5-VBSTx</sub> , I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	0.7	0.8	0.9	V
I <sub>VBSTLK</sub>	VBST leakage current	VBSTx = 29 V, SWx = 24 V, T <sub>A</sub> = 25°C		0.1	1	μA

(1) Not production tested - ensured by design.

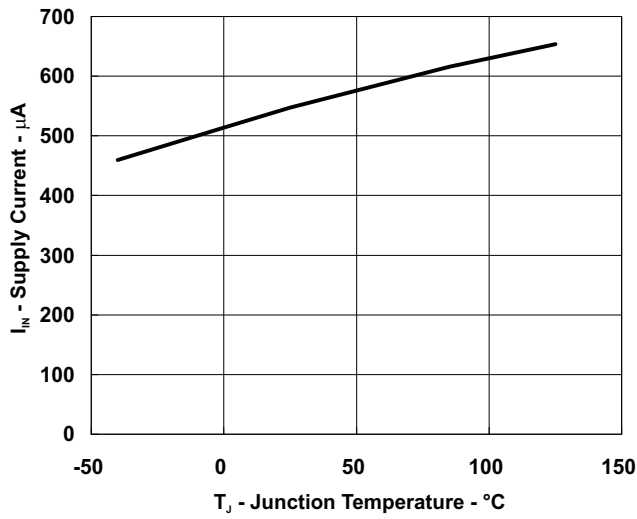
## Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

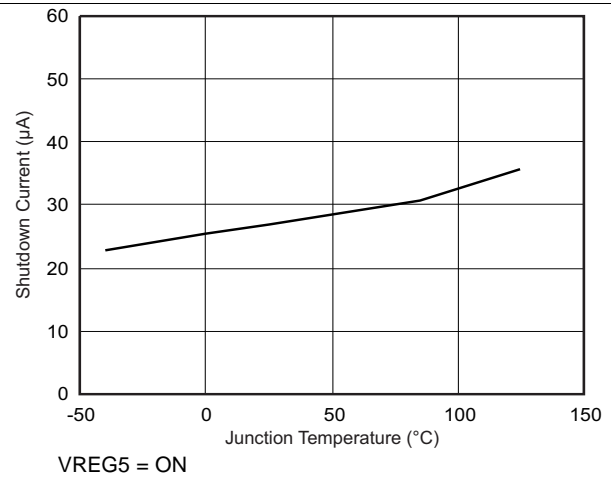
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ON-TIME TIMER CONTROL						
T <sub>ON1L</sub>	CH1 on time	SW1 = 12 V, VO1 = 1.8 V		490		ns
T <sub>ON2L</sub>	CH2 on time	SW2 = 12 V, VO2 = 1.8 V		390		ns
T <sub>OFF1L</sub>	CH1 min off time	SW1 = 0.7 V, T <sub>A</sub> = 25°C, VFB1 = 0.7 V		285		ns
T <sub>OFF2L</sub>	CH2 min off time	SW2 = 0.7 V, T <sub>A</sub> = 25°C, VFB2 = 0.7 V		285		ns
SOFT START						
I <sub>SSC</sub>	SS1/SS2 charge current	V <sub>SS1</sub> /V <sub>SS2</sub> = 0 V, T <sub>A</sub> = 25°C	–2.5	–2	–1.5	μA
TC <sub>ISSC</sub>	I <sub>SSC</sub> temperature coefficient	On the basis of 25°C <sup>(2)</sup>	–4		3	nA/°C
I <sub>SSD</sub>	SS1/SS2 discharge current	V <sub>SS1</sub> /V <sub>SS2</sub> = 0.5 V	100	150		μA
UVLO						
V <sub>UV5VFILT</sub>	V5FILT UVLO threshold	Wake up	3.7	4.0	4.3	V
		Hysteresis	0.2	0.3	0.4	
LOGIC THRESHOLD						
V <sub>ENH</sub>	ENx high-level input voltage	EN 1/2	2.0			V
V <sub>ENL</sub>	ENx low-level input voltage	EN 1/2			0.3	V
CURRENT SENSE						
I <sub>TRIP</sub>	TRIP source current	V <sub>TRIPx</sub> = 0.1 V, T <sub>A</sub> = 25°C	8.5	10	11.5	μA
TC <sub>ITRIP</sub>	I <sub>TRIP</sub> temperature coefficient	On the basis of 25°C		4000		ppm/°C
V <sub>OCLoff</sub>	OCP compensation offset	(V <sub>TRIPx-GND</sub> -V <sub>PGNDx-SWx</sub> ) voltage, V <sub>TRIPx-GND</sub> = 60 mV, T <sub>A</sub> = 25°C	–15	0	15	mV
		(V <sub>TRIPx-GND</sub> -V <sub>PGNDx-SWx</sub> ) voltage, V <sub>TRIPx-GND</sub> = 60 mV	–20		20	
V <sub>Rtrip</sub>	Current limit threshold setting range	V <sub>TRIPx-GND</sub> voltage	30		300	mV
OUTPUT UNDERVOLTAGE AND OVERVOLTAGE PROTECTION						
V <sub>OVP</sub>	Output OVP trip threshold	OVP detect	110	115	120	%
T <sub>OVPDEL</sub>	Output OVP prop delay			1.5		μs
V <sub>UVP</sub>	Output UVP trip threshold	UVP detect	65	70	75	%
		Hysteresis (recover < 20 μs)		10		
T <sub>UVPDEL</sub>	Output UVP delay		17	30	40	μs
T <sub>UVPEN</sub>	Output UVP enable delay	UVP enable delay / soft-start time	x1.4	x1.7	x2.0	ms
THERMAL SHUTDOWN						
T <sub>SDN</sub>	Thermal shutdown threshold	Shutdown temperature <sup>(2)</sup>		150		°C
		Hysteresis <sup>(2)</sup>		20		

(2) Not production tested - ensured by design.

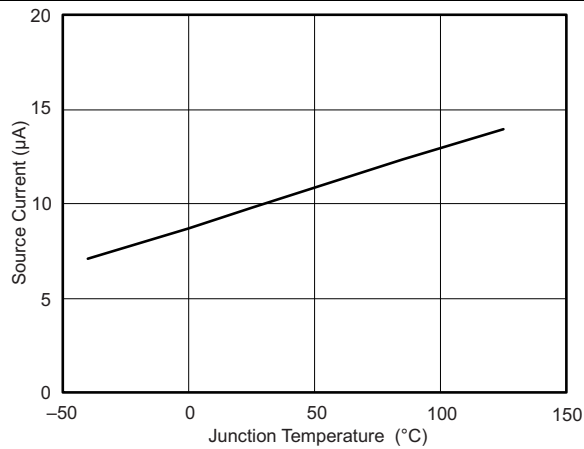
## 6.6 Typical Characteristics



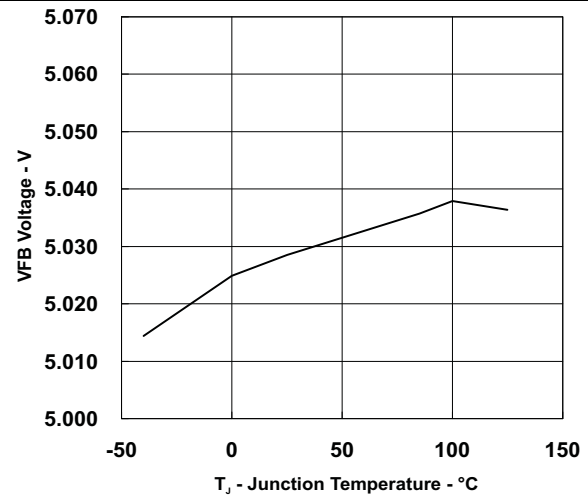
**Figure 1. VIN Supply Current  
vs  
Junction Temperature**



**Figure 2. VIN Shutdown Current  
vs  
Junction Temperature**

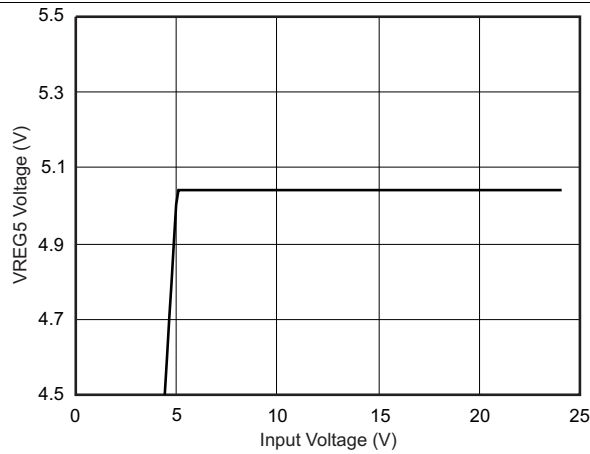


**Figure 3. Trip Source Current  
vs  
Junction Temperature**

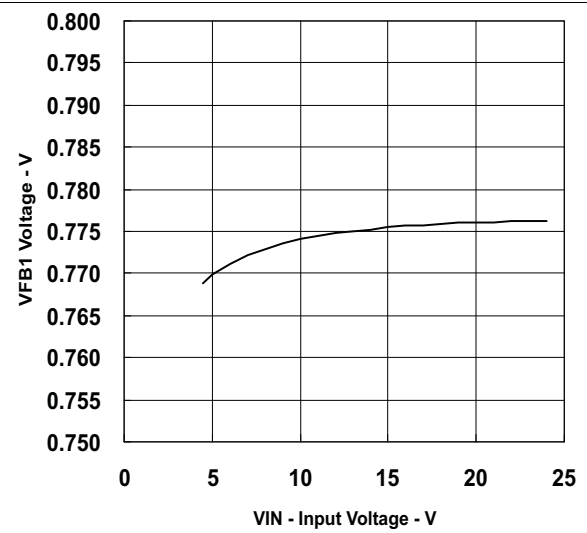


**Figure 4. VREG5 Voltage  
vs  
Junction Temperature**

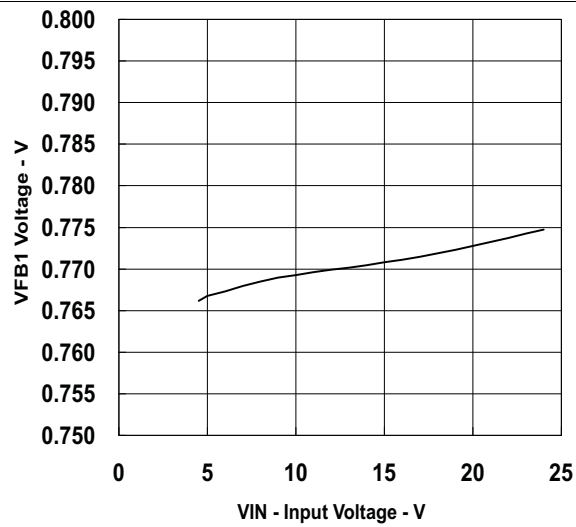
## Typical Characteristics (continued)



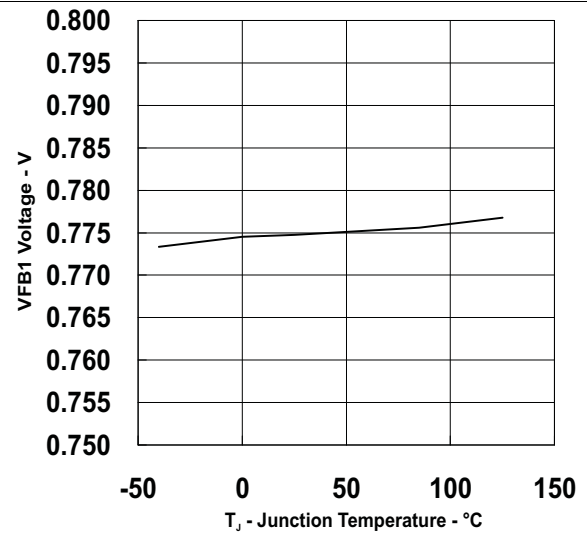
**Figure 5. VREG5 Voltage  
vs  
Input Voltage**



**Figure 6. VFB1 Voltage  
vs  
Input Voltage**



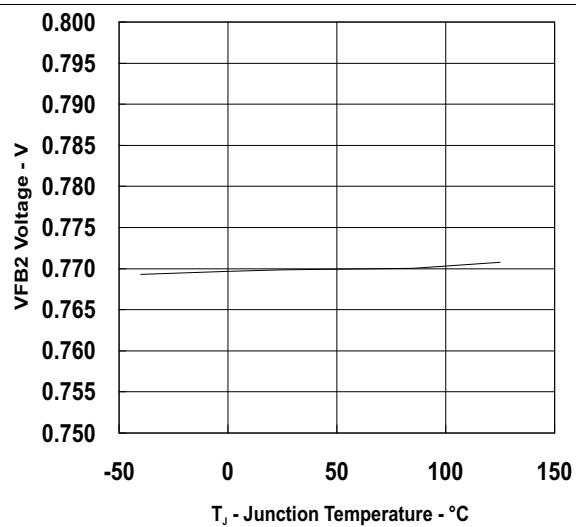
**Figure 7. VFB2 Voltage  
vs  
Input Voltage**



**Figure 8. VFB1 Voltage  
vs  
Junction Temperature**



## Typical Characteristics (continued)



**Figure 9. VFB2 Voltage  
vs  
Junction Temperature**

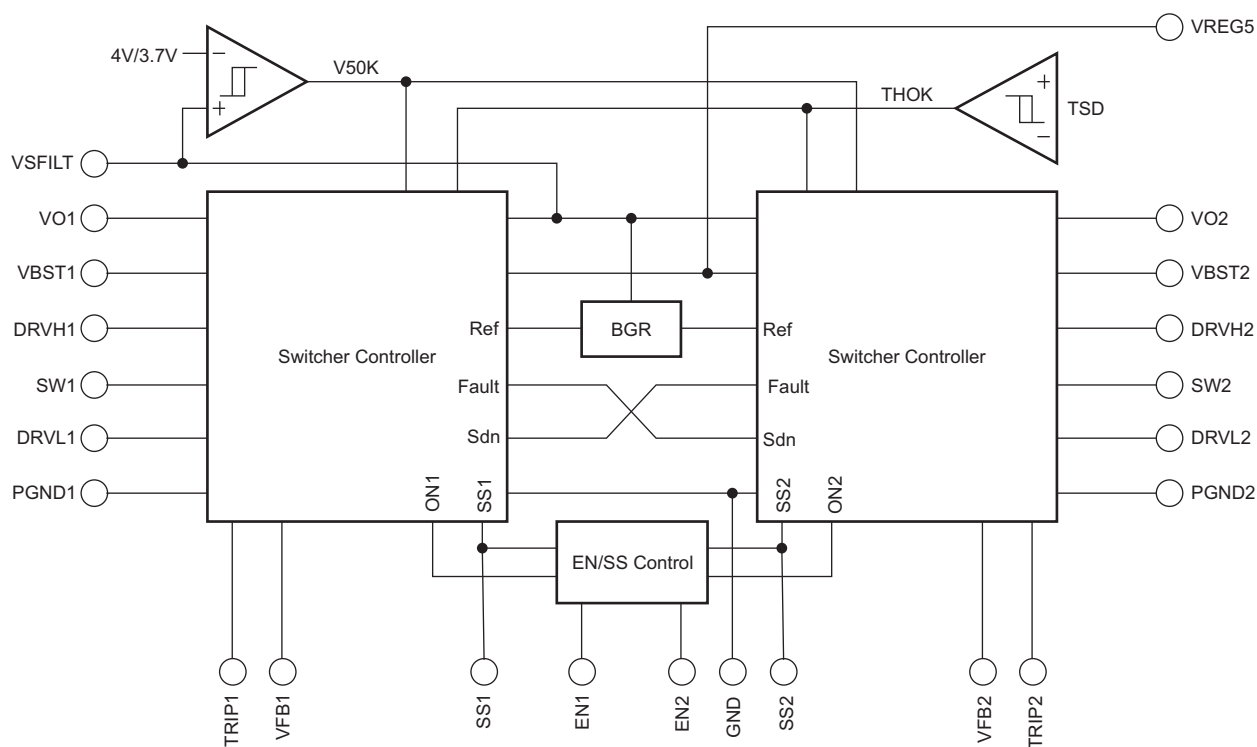
## 7 Detailed Description

### 7.1 Overview

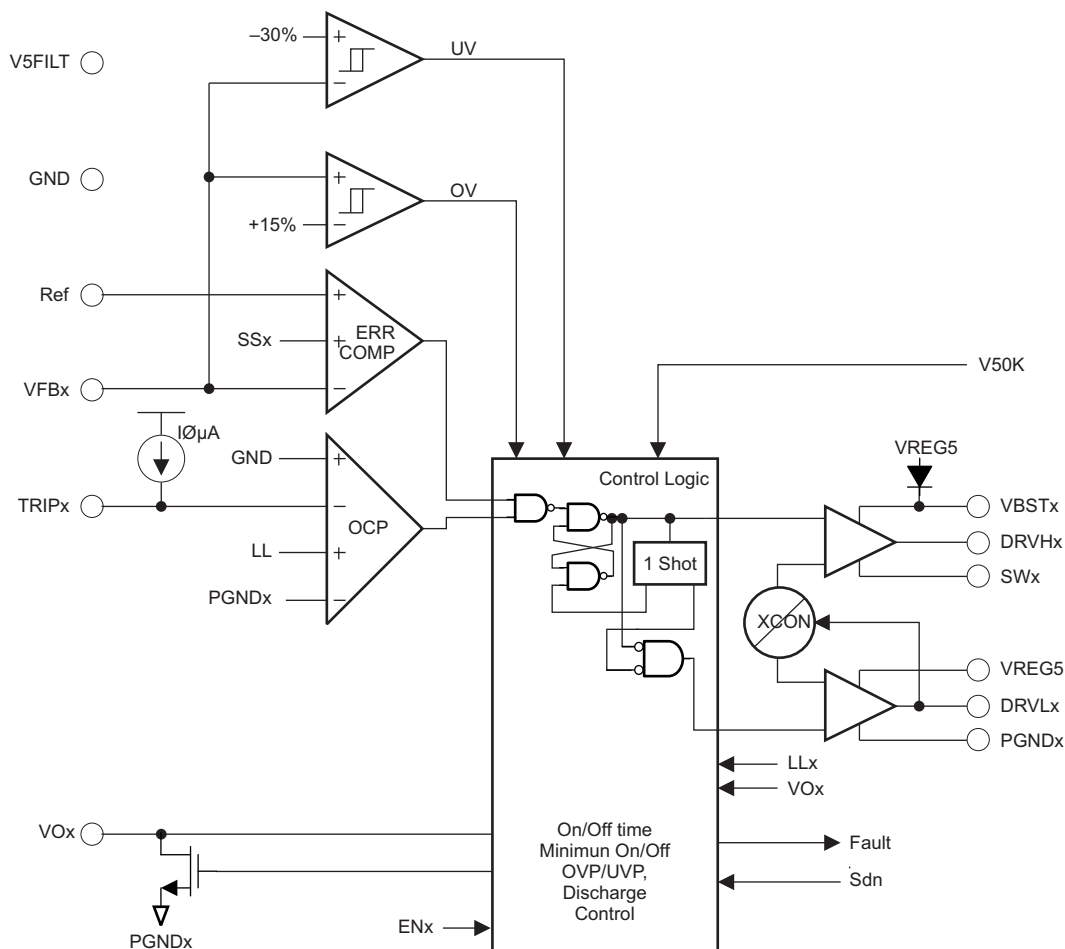
The TPS53128 is a dual, adaptive on-time D-CAP2™ mode synchronous buck controller. The part enables system designers to cost-effectively complete the suite of various end equipment power bus regulators with a low external component count and low standby consumption. The main control loop for the TPS53128 uses the D-CAP2™ Mode topology, which provides a fast transient response with no external component.

The TPS53128 also has a proprietary circuit that enables the device to adapt not only low equivalent series resistance (ESR) output capacitors such as POSCAP/SP-CAP, but also to ceramic capacitors. The fixed frequency, emulated adaptive on-time control supports seamless operation between PWM mode at heavy load condition and reduced frequency operation at light load for high efficiency, down to the milliampere range. The part provides a convenient and efficient operation, with conversion voltages from 4.5 to 24 V and output voltage from 0.76 to 5.5 V.

### 7.2 Functional Block Diagram



## Functional Block Diagram (continued)



## 7.3 Feature Description

### 7.3.1 PWM Operation

The main control loop of the TPS53128 is an adaptive on-time pulse width modulation (PWM) controller using a proprietary D-CAP2™ mode control. D-CAP2™ mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the synchronous high-side MOSFET is turned on. After an internal one-shot timer expires, this MOSFET is turned off. When the feedback voltage falls below the reference voltage, the one-shot timer is reset and the high-side MOSFET is turned back on. The one shot is set by the converter input voltage VIN, and the output voltage VO, to maintain a pseudo-fixed frequency over the input voltage range. An internal ramp is added to the reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP mode control.

### 7.3.2 Light-Load Condition

TPS53128 automatically reduces switching frequency at light-load conditions to maintain high efficiency. This reduction of frequency is achieved smoothly and without increase of VOUT ripple or load regulation. Detail operation is described as follows. As the output current decreases from heavy-load condition, the inductor current is also reduced, and eventually comes to the point that its valley touches zero current, which is the boundary between continuous conduction and discontinuous condition modes. The low-side MOSFET is turned off when this zero inductor current is detected. As the load current is further decreased, the converter runs in

## Feature Description (continued)

discontinuous conduction mode and it takes longer and longer to discharge the output capacitor to the level that requires the next ON cycle. The ON time is kept the same as that in the heavy-load condition. In reverse, when the output current increases from light load to heavy load, the switching frequency increases to the preset value as the inductor current reaches the continuous conduction. The transition load point to the light load operation,  $I_{OUT(LL)}$  (i.e., threshold between continuous and discontinuous condition mode) can be calculated as follows.

$$I_{OUT(LL)} = \frac{1}{2 \times L \times f_{SW}} \frac{V_{IN} - V_{OX}}{V_{IN}} \times V_{OX} \quad (1)$$

Where  $f_{SW}$  is the PWM switching frequency.

Switching frequency versus output current in the light-load condition is a function of  $L$ ,  $f_{SW}$ ,  $V_{IN}$  and  $V_{OUT}$ , but it decreases almost proportional to the output current from the  $I_{OUT(LL)}$  given in [Equation 1](#).

### 7.3.3 Drivers

Each channel of the TPS53128 contains two high-current resistive MOSFET gate drivers. The low-side driver is a PGND referenced, VREG5 powered driver designed to drive the gate of a high-current, low  $R_{DS(ON)}$  N-channel MOSFET whose source is connected to PGND. The high-side driver is a floating SWx referenced VBST powered driver designed to drive the gate of a high-current, low  $R_{DS(ON)}$  N-channel MOSFET. To maintain the VBST voltage during the high-side driver ON time, a capacitor is placed from SWx to VBSTx. Each driver draws average current equal to gate charge ( $Q_g$  at  $V_{gs} = 5\text{ V}$ ) times switching frequency ( $f_{SW}$ ).

To prevent cross-conduction, there is a narrow dead-time when both high-side and low-side drivers are OFF between each driver transition. During this time the inductor current is carried by one of the MOSFETs body diodes.

### 7.3.4 PWM Frequency And Adaptive On-Time Control

TPS53128 employs adaptive on-time control scheme and does not have a dedicated on board oscillator.

TPS53128 runs with pseudo-constant frequency by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage. Therefore, when the duty ratio is  $V_{OUT}/V_{IN}$ , the frequency is constant.

### 7.3.5 5-Volt Regulator

The TPS53128 has an internal 5-V low-dropout (LDO) regulator to provide a regulated voltage for all both drivers and the IC's internal logic. A high-quality 4.7- $\mu\text{F}$  or greater ceramic capacitor from VREG5 to GND is required to stabilize the internal regulator. An internal 10- $\Omega$  resistor from VREG5 filters the regulator output to the IC's analog and logic input voltage, V5FILT. An additional high-quality 1.0- $\mu\text{F}$  ceramic capacitor is required from V5FILT to GND to filter switching noise from VREG5.

### 7.3.6 Soft Start

The TPS53128 has a programmable soft-start. When the ENx pin becomes high, 2.0- $\mu\text{A}$  current begins charging the capacitor connected from the SS pin to GND. The internal reference for the D-CAP2™ mode control comparator is overridden by the soft-start voltage until the soft-start voltage is greater than the internal reference for smooth control of the output voltage during start up.

### 7.3.7 Pre-Bias Support

The TPS53128 supports pre-bias start-up without sinking current from the output capacitor. When enabled, the low-side driver is held off until the soft-start commands a voltage higher than the pre-bias level (internal soft-start becomes greater than feedback voltage (VFB)), then the TPS53128 slowly activates synchronous rectification by limiting the first DRV1 pulses with a narrow on-time. This limited on-time is then incremented on a cycle-by-cycle basis until it coincides with the full 1-D off-time. This scheme prevents the initial sinking of current from the pre-bias output, and ensure that the output voltage (VOUT) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

## Feature Description (continued)

### 7.3.8 Output Discharge Control

TPS53128 discharges the outputs when ENx is low, or the controller is turned off by the protection functions (OVP, UVP, UVLO, and thermal shutdown). The device discharges output using an internal 40-Ω MOSFET which is connected to VOx and PGNDx. The external low-side MOSFET is not turned on during the output discharge operation to avoid the possibility of causing negative voltage at the output. This discharge ensures that on start the regulated voltage always initializes from 0 V.

### 7.3.9 Over Current Limit

TPS53128 has cycle-by-cycle over current limit feature. The over current limits the inductor valley current by monitoring the voltage drop across the low-side MOSFET  $R_{DS(ON)}$  during the low-side driver on-time. If the inductor current is larger than the over current limit (OCL), the TPS53128 delays the start of the next switching cycle until the sensed inductor current falls below the OCL current. MOSFET  $R_{DS(ON)}$  current sensing is used to provide an accuracy and cost effective solution without external devices. To program the OCL, the TRIP pin should be connected to GND through a trip voltage setting resistor, according to the following equations.

$$V_{TRIP} = \left( I_{OCL} - \frac{(V_{IN} - V_O)}{2 \cdot L1 \cdot f_{SW}} \cdot \frac{V_O}{V_{IN}} \right) \cdot R_{DS(ON)} \quad (2)$$

$$R_{TRIP} (k\Omega) = \frac{V_{TRIP} (mV)}{I_{TRIP} (\mu A)} \quad (3)$$

The trip voltage should be between 30 mV to 300 mV over all operational temperature, including the 4000-ppm/°C temperature slope compensation for the temperature dependency of the  $R_{DS(ON)}$ .

If the load current exceeds the over current limit, the voltage will begin to drop. If the over current conditions continues the output voltage will fall below the under voltage protection threshold and the TPS53128 will shut down.

In an over current condition, the current to the load exceeds the current to the output capacitor; thus the output voltage tends to fall off. Eventually, it will end up with crossing the under voltage protection threshold and shutdown.

### 7.3.10 Over/Under Voltage Protection

TPS53128 monitors a resistor divided feedback voltage to detect over and under voltage. If the feedback voltage is higher than 115% of the reference voltage, the OVP comparator output goes high and the circuit latches the high-side MOSFET driver OFF and the low-side MOSFET driver ON.

When the feedback voltage is lower than 70% of the reference voltage, the UVP comparator output goes high and an internal UVP delay counter begins counting. After 30 μs, TPS53128 latches OFF both top and bottom MOSFET drivers. This function is enabled approximately  $1.7 \times T_{SS}$  after power-on. The OVP and UVP latch off is reset when EN goes low level.

### 7.3.11 UVLO Protection

TPS53128 has V5FILT under voltage lock out protection (UVLO) that monitors the voltage of V5FILT pin.

When the V5FILT voltage is lower than UVLO threshold voltage, the device is shut off. All output drivers are OFF and output discharge is ON. The UVLO is non-latch protection.

### 7.3.12 Thermal Shutdown

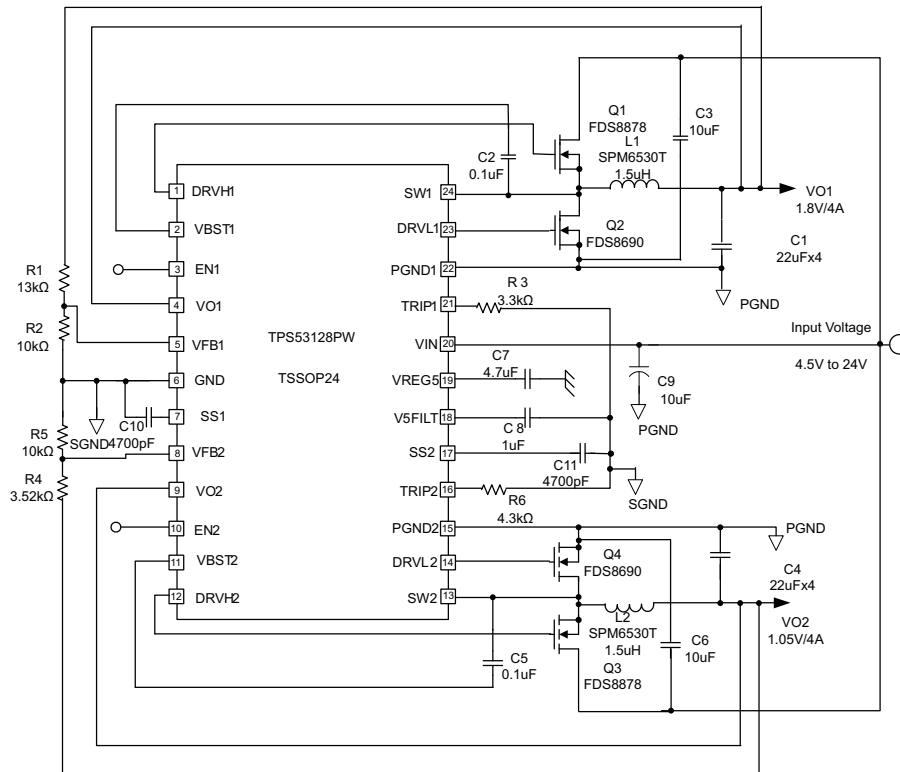
The TPS53128 includes an over temperature protection shut-down feature. If the TPS53128 die temperature exceeds the OTP threshold (typically 150°C), both the high-side and low-side drivers are shut off, the output voltage discharge function is enabled and then the device is shut off until the die temperature drops. Thermal shutdown is a non-latch protection.

## 7.4 Device Functional Modes

The TPS53128 has two operating modes. The TPS53128 is in shut down mode when the EN1 and EN2 pins are low. When the EN1 and EN2 pins are pulled high, the TPS53128 enters the normal operating mode.



## Typical Application (continued)



**Figure 11. TSSOP**

### 8.2.1 Design Requirements

**Table 3. Design Parameters**

DESIGN PARAMETER	EXAMPLE VALUE
Input Voltage	12 V
Output Voltage	Vo1 = 1.8 V Vo2 = 1.05 V

### 8.2.2 Detailed Design Procedure

#### 1. Choose inductor.

The inductance value is selected to provide approximately 30% peak to peak ripple current at maximum load. Larger ripple current increases output ripple voltage, improve S/N ratio and contribute to stable operation.

Equation 4 can be used to calculate L1.

$$L1 = \frac{(V_{IN(max)} - V_{O1})}{I_{L(ripple)} \times f_{SW}} \times \frac{V_{O1}}{V_{IN(max)}} = \frac{3 \times (V_{IN(max)} - V_{O1})}{I_{O1} \times f_{SW}} \times \frac{V_{O1}}{V_{IN(max)}} \quad (4)$$

The inductors current ratings needs to support both the RMS (thermal) current and the Peak (saturation) current. The RMS and peak inductor current can be estimated as follows.

$$I_{L(RIPPLE)} = \frac{V_{IN(MAX)} - V_{O1}}{L1 \cdot f_{SW}} \cdot \frac{V_{O1}}{V_{IN(MAX)}} \quad (5)$$



$$I_{L1(PEAK)} = \frac{V_{TRIP}}{R_{DS(ON)}} + I_{L1(RIPPLE)} \quad (6)$$

$$I_{L1(RMS)} = \sqrt{I_{O1}^2 + \frac{1}{12} (I_{L1(RIPPLE)})^2} \quad (7)$$

Note: The calculation above shall serve as a general reference. To further improve transient response, the output inductance could be reduced further. This needs to be considered along with the selection of the output capacitor.

## 2. Choose output capacitor.

The capacitor value and ESR determines the amount of output voltage ripple and load transient response. It is recommended to use a ceramic output capacitor.

$$C1 = \frac{I_{L1(RIPPLE)}}{8 \cdot V_{O1} \cdot f_{SW}} \cdot \frac{1}{f_{SW}} \quad (8)$$

$$C1 = \frac{\Delta I_{load}^2 \cdot L1}{2 \cdot V_{O1} \cdot \Delta V_{OS}} \quad (9)$$

$$C1 = \frac{\Delta I_{load}^2 \cdot L1}{2 \cdot K \cdot \Delta V_{US}} \quad (10)$$

Where

$$K = (V_{IN} - V_{O1}) \cdot \frac{T_{on}}{T_{on} + T_{min(off)}} \quad (11)$$

Select the capacitance value greater than the largest value calculated from [Equation 8](#), [Equation 9](#) and [Equation 10](#). The capacitance for C1 should be greater than 66 µF.

Where

$\Delta V_{OS}$  = The allowable amount of overshoot voltage in load transition

$\Delta V_{US}$  = The allowable amount of undershoot voltage in load transition

$T_{min(off)}$  = Minimum off time

## 3. Choose input capacitor.

The TPS53128 requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A minimum 10-µF high-quality ceramic capacitor is recommended for the input capacitor. The capacitor voltage rating needs to be greater than the maximum input voltage.

## 4. Choose bootstrap capacitor.

The TPS53128 requires a bootstrap capacitor from SW to VBST to provide the floating supply for the high-side drivers. A minimum 0.1-µF high-quality ceramic capacitor is recommended. The voltage rating should be greater than 10 V.

## 5. Choose VREG5 and V5FILT capacitor.

The TPS53128 requires both the VREG5 regulator and V5FILT input are bypassed. A minimum 4.7-µF high-quality ceramic capacitor must be connected between the VREG5 and GND for proper operation. A minimum 1-µF high-quality ceramic capacitor must be connected between the V5FILT and GND for proper operation. Both of these capacitors' voltage ratings should be greater than 10 V.

## 6. Choose output voltage divider resistors.

The output voltage is set with a resistor divider from the output voltage node to the VFBx pin. It is recommended to use 1% tolerance or better resistors. Select R2 between 10 kΩ and 100 kΩ and use [Equation 12](#) or [Equation 13](#) to calculate R1.

$$V_{swinj} = (V_{IN} - V_{O1} \cdot 0.5875) \cdot \left(\frac{1}{f_{SW}}\right) \cdot \left(\frac{V_{O1}}{V_{IN}}\right) \cdot 4975 \quad (12)$$

$$R1 = \left( \frac{V_o1}{V_{FB} + \frac{V_{FB(RIPPLE)} + V_{swinj}}{2}} - 1 \right) \cdot R2 \quad (13)$$

Where

$V_{FB(RIPPLE)}$  = Ripple voltage at VFB

$V_{swinj}$  = Ripple voltage at error comparator

7. Choose register setting for over current limit.

$$V_{TRIP} = \left( I_{OCL} - \frac{(V_{IN} - V_o)}{2 \cdot L1 \cdot f_{SW}} \cdot \frac{V_o}{V_{IN}} \right) \cdot R_{DS(ON)} \quad (14)$$

$$R_{TRIP} (k\Omega) = \frac{V_{TRIP} (mV) - V_{OCLoff}}{I_{TRIP(min)} (\mu A)} \quad (15)$$

Where

$R_{DS(ON)}$  = Low side FET on-resistance

$I_{TRIP(min)}$  = TRIP pin source current ( 8.5  $\mu A$  )

$V_{OCLoff}$  = Minimum over current limit offset voltage (–20 mV)

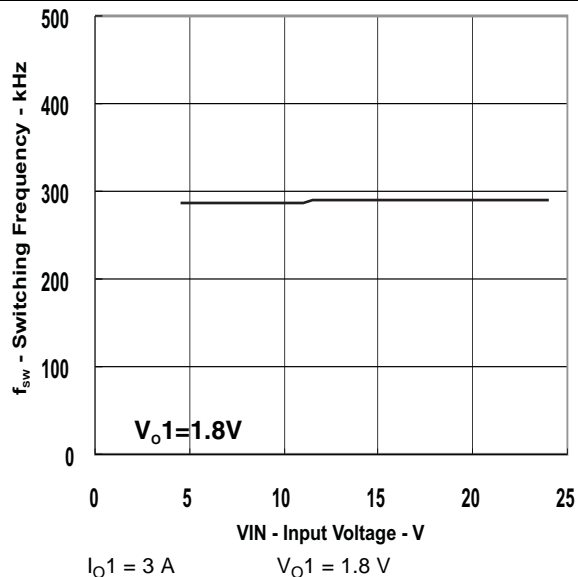
$I_{OCL}$  = Over current limit

8. Choose soft start capacitor.

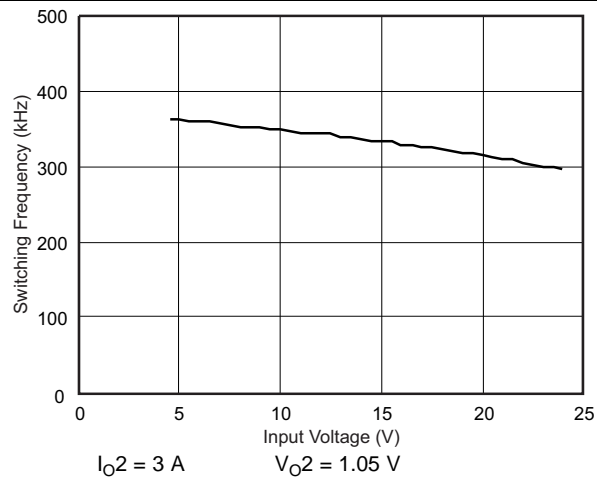
Soft start time equation is as follows.

$$C_{SS} = \frac{T_{SS} \cdot I_{SSC}}{V_{FB}} \quad (16)$$

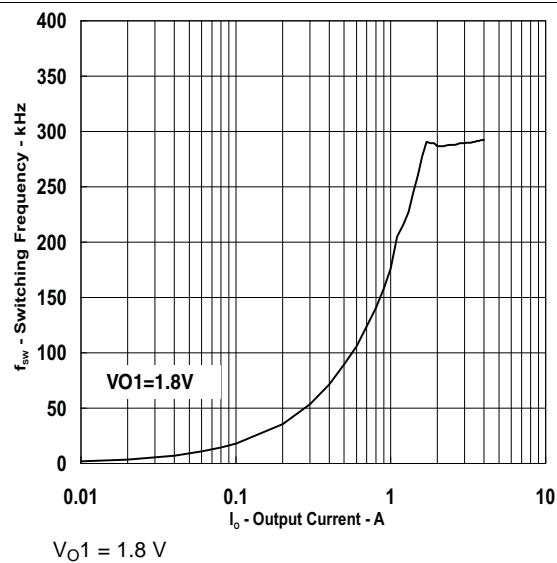
## 8.2.3 Application Curves



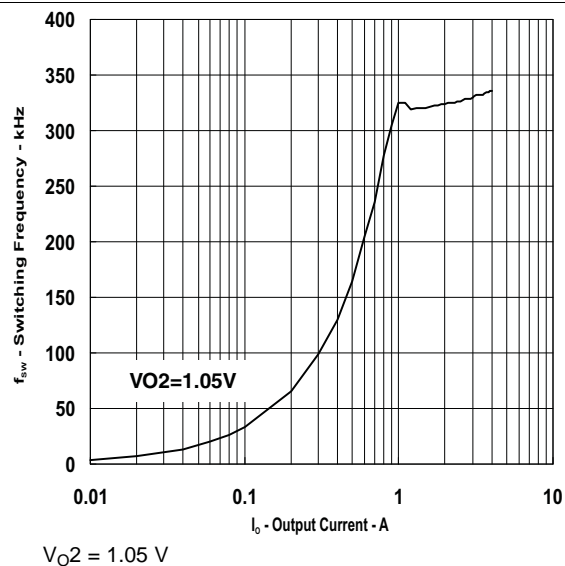
**Figure 12. Switching Frequency  
vs  
Input Voltage (Ch1)**



**Figure 13. Switching Frequency  
vs  
Input Voltage (Ch2)**



**Figure 14. Switching Frequency  
vs  
Output Current (Ch1)**



**Figure 15. Switching Frequency  
vs  
Output Current (Ch2)**

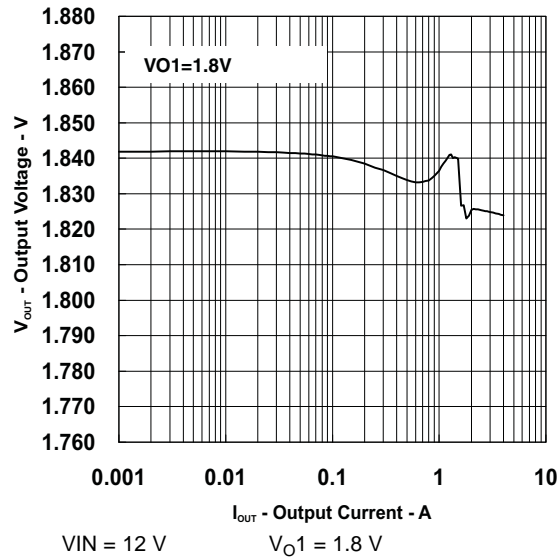


Figure 16. Output Voltage  
vs  
Output Current (Ch1)

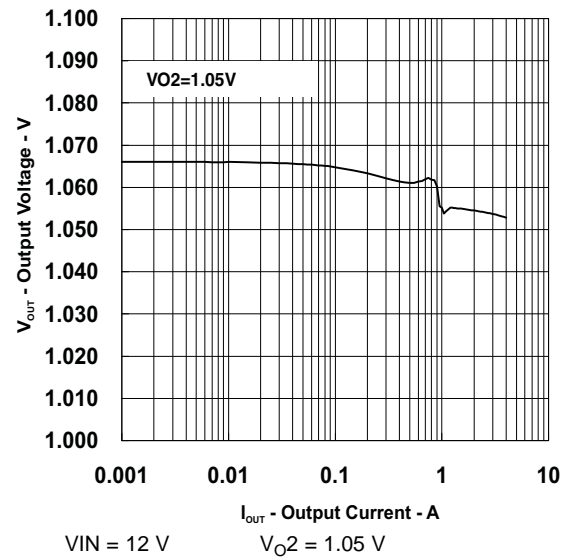


Figure 17. Output Voltage  
vs  
Output Current (Ch2)

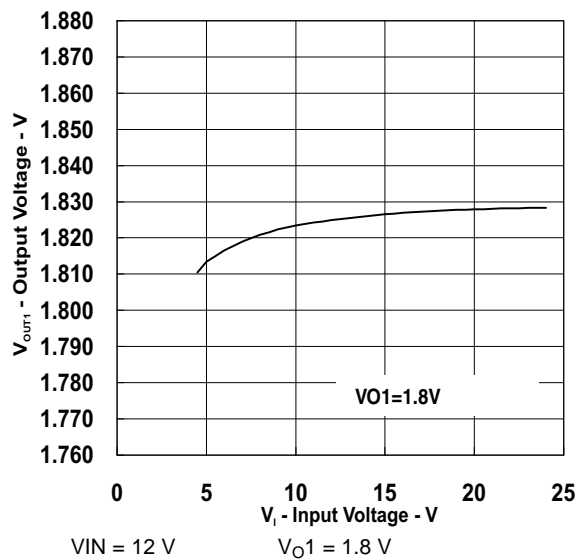


Figure 18. Output Voltage  
vs  
Input Voltage (Ch1)

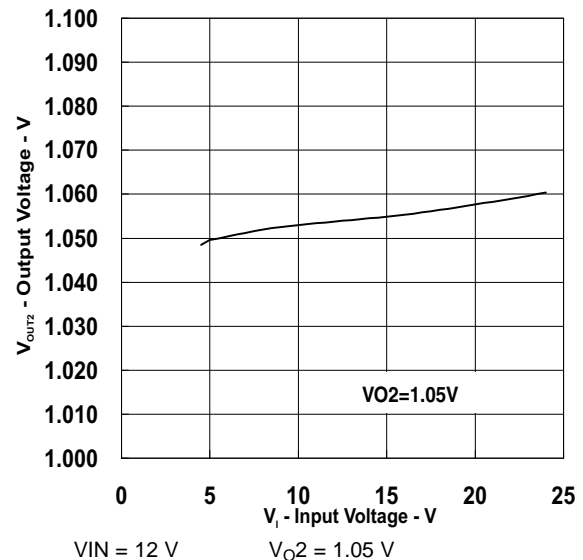


Figure 19. Output Voltage  
vs  
Input Voltage (Ch2)

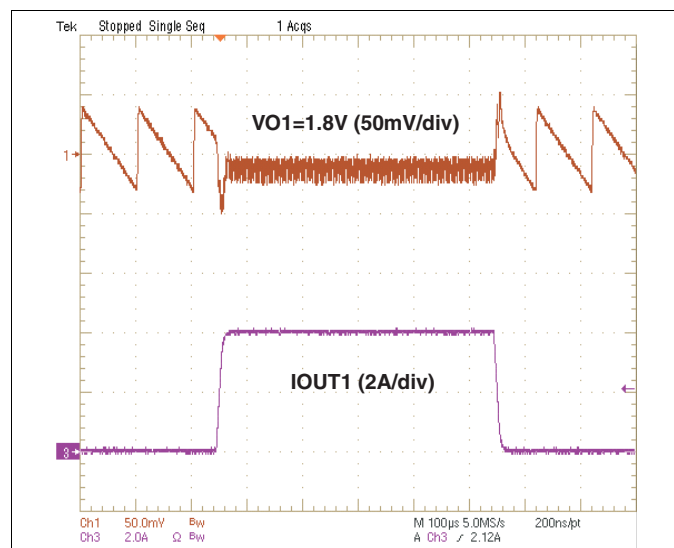


Figure 20. Load Transient Response

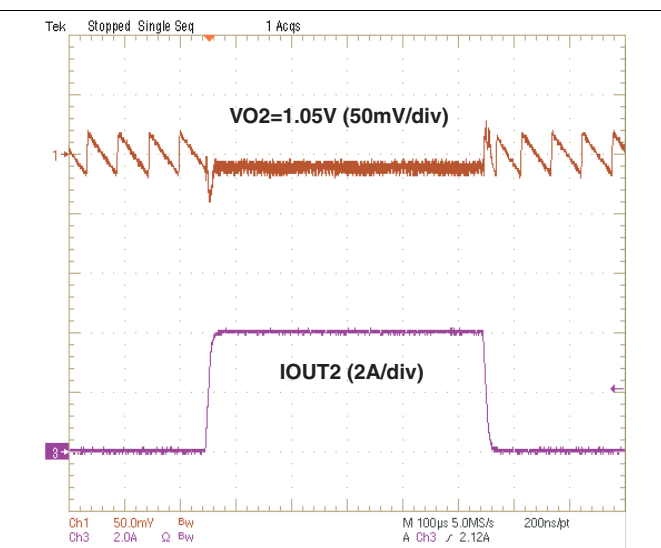


Figure 21. Load Transient Response

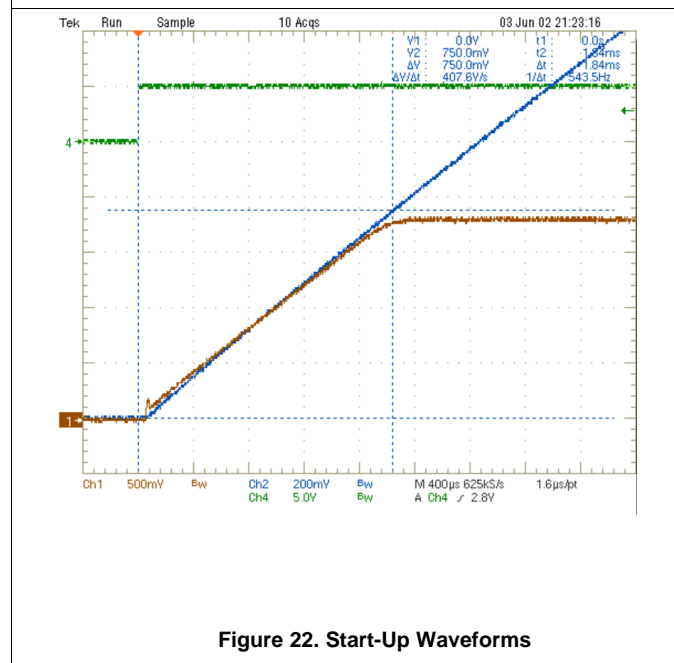


Figure 22. Start-Up Waveforms

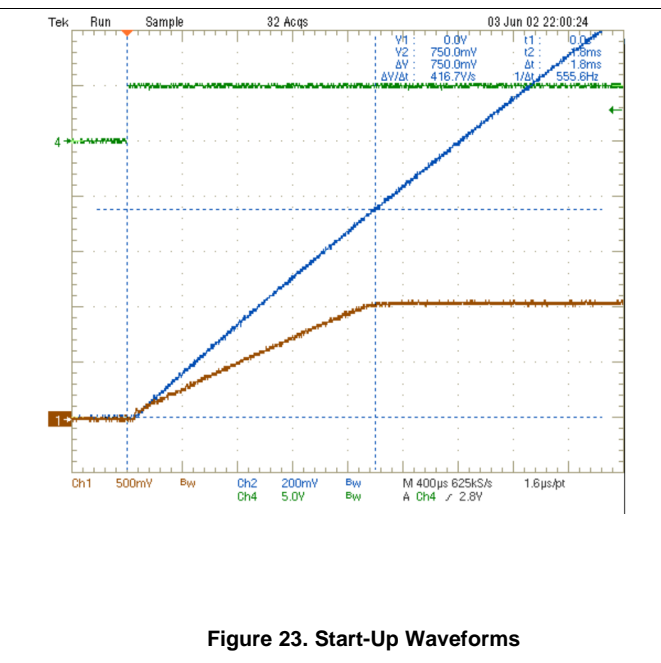
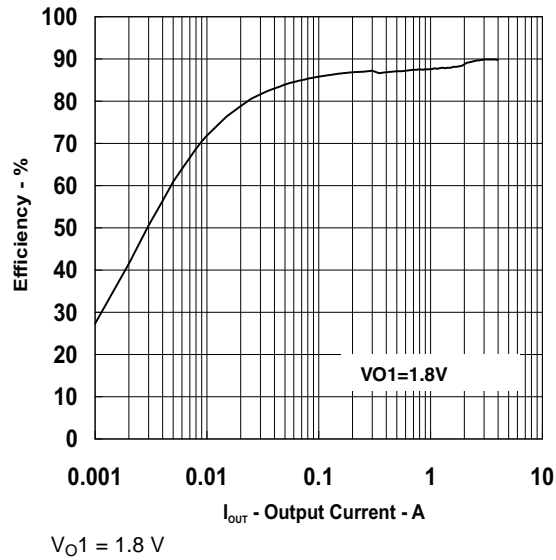
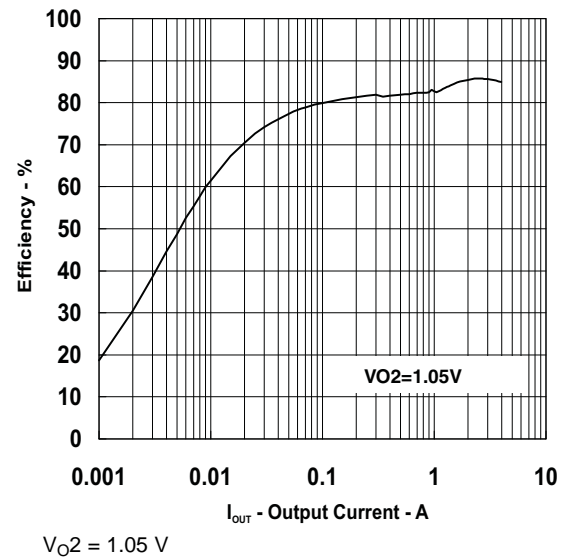


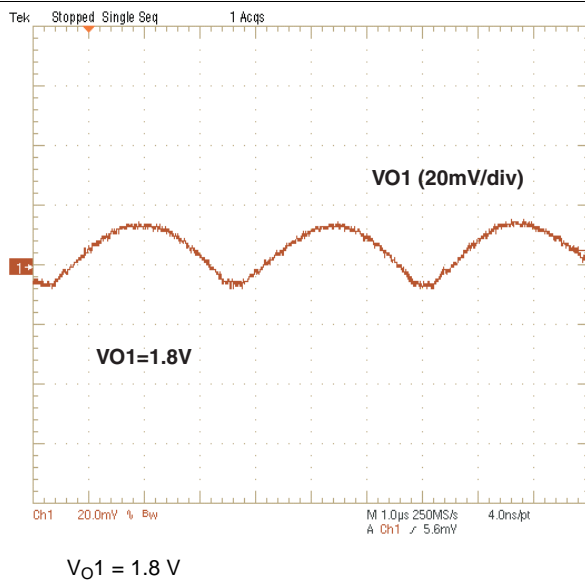
Figure 23. Start-Up Waveforms



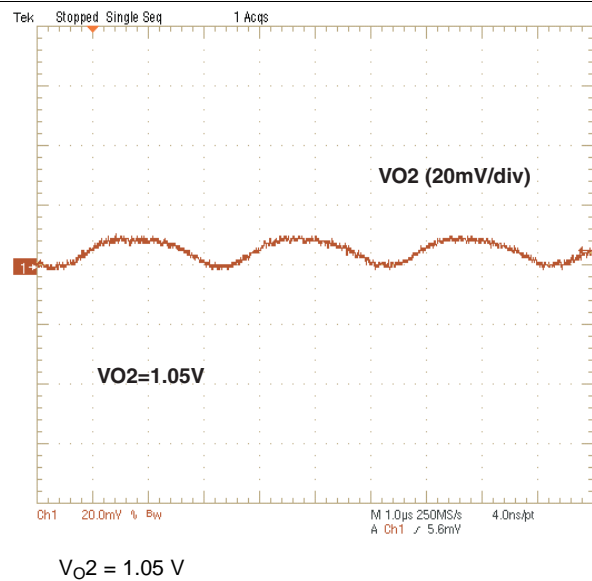
**Figure 24. 1.8-V Efficiency  
vs  
Output Current (Ch1)**



**Figure 25. 1.05-V Efficiency  
vs  
Output Current (Ch2)**



**Figure 26. 1.8-V Output Ripple Voltage**



**Figure 27. 1.05-V Output Ripple Voltage**

## 9 Power Supply Recommendations

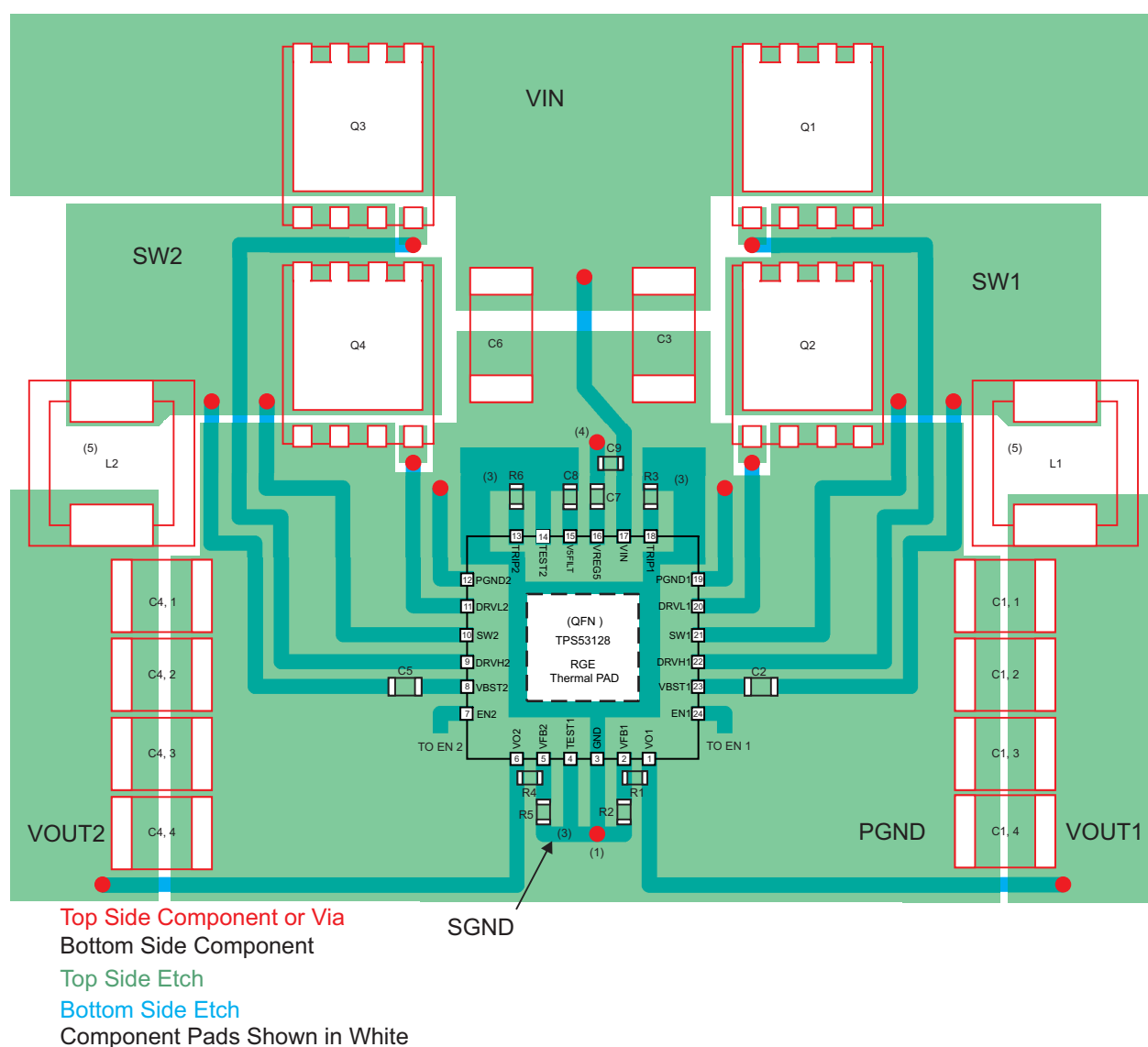
The devices are designed to operate from an input voltage supply range between 4.5 and 24 V. This input supply must be well regulated. If the input supply is located more than a few inches from the TPS53128 device, an additional 0.1  $\mu\text{F}$  ceramic capacitance may be required in addition to the 10  $\mu\text{F}$  of the ceramic bypass capacitors.

## 10 Layout

### 10.1 Layout Guidelines

- Keep the input switching current loop as small as possible.
- Place the input capacitor (C3,C6) close to the top switching FET. The output current loop should also be kept as small as possible.
- Keep the SW node as physically small and short as possible as to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin (FBx) of the device.
- Keep analog and non-switching components away from switching components.
- Make a single point connection from the signal ground to power ground.
- Do not allow switching current to flow under the device.

### 10.2 Layout Example



**Figure 28.**



## 11 Device and Documentation Support

### 11.1 Trademarks

Eco-mode, D-CAP2 are trademarks of Texas Instruments.  
All other trademarks are the property of their respective owners.

### 11.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 11.3 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
TPS53128PW	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TPS53128	<a href="#">Samples</a>
TPS53128PWR	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	TPS53128	<a href="#">Samples</a>
TPS53128RGER	ACTIVE	VQFN	RGE	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TPS 53128	<a href="#">Samples</a>
TPS53128RGET	ACTIVE	VQFN	RGE	24	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	TPS 53128	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

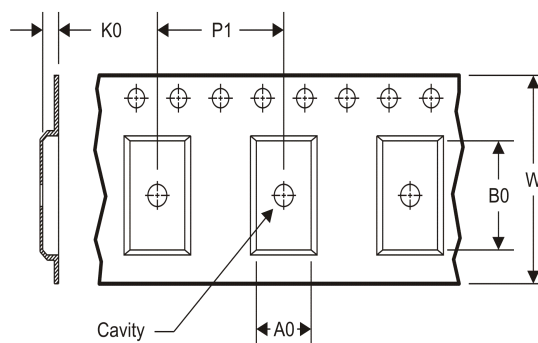
(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



**TAPE AND REEL INFORMATION**
**REEL DIMENSIONS**

**TAPE DIMENSIONS**


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

**TAPE AND REEL INFORMATION**

\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS53128PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
TPS53128RGER	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TPS53128RGET	VQFN	RGE	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS53128PWR	TSSOP	PW	24	2000	367.0	367.0	38.0
TPS53128RGER	VQFN	RGE	24	3000	367.0	367.0	35.0
TPS53128RGET	VQFN	RGE	24	250	210.0	185.0	35.0

PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



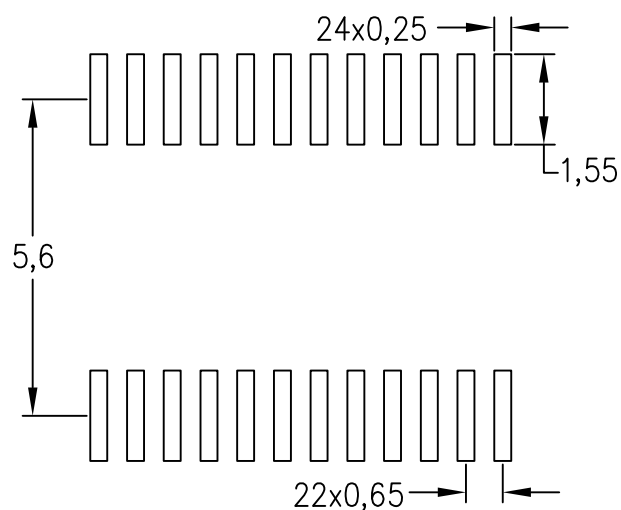
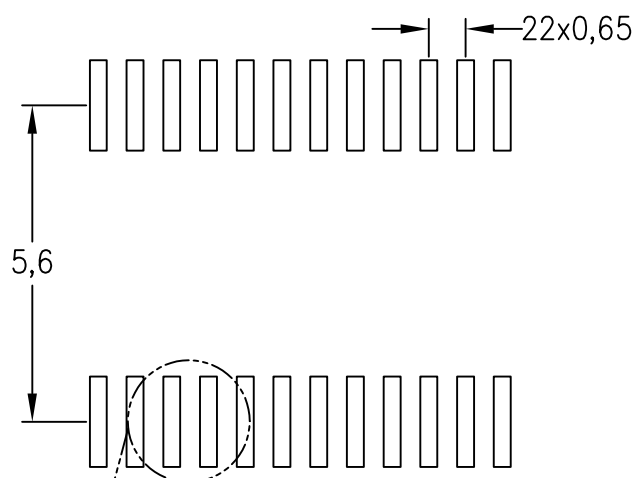
- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - $\Delta$  C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  - $\Delta$  D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE

Example Board Layout

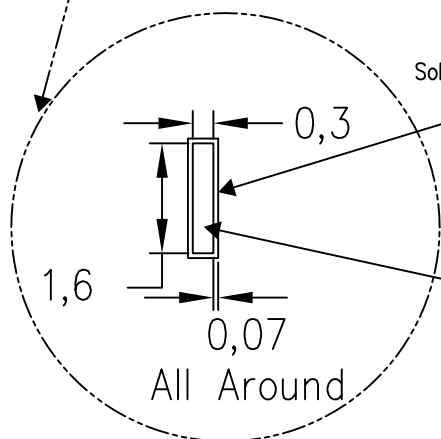
Stencil Openings  
Based on a stencil thickness  
of .127mm (.005inch).



Example  
Non Soldermask Defined Pad

Example  
Solder Mask Opening  
(See Note F)

Pad Geometry

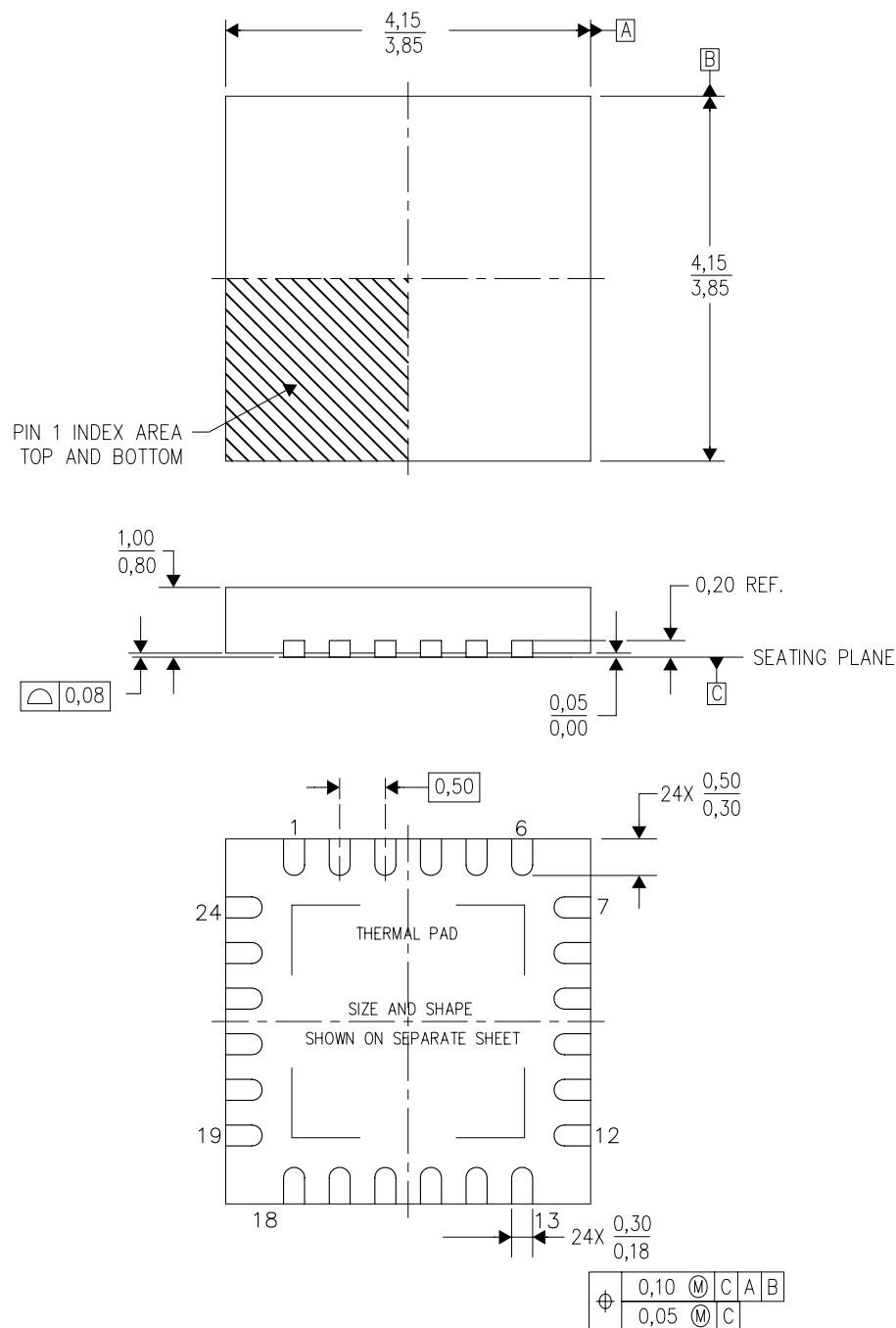


4211284-4/F 12/12

- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate design.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

RGE (S-PVQFN-N24)

PLASTIC QUAD FLATPACK NO-LEAD



4204104/G 07/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-Leads (QFN) package configuration.
  - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - F. Falls within JEDEC MO-220.



## THERMAL PAD MECHANICAL DATA

RGE (S-PVQFN-N24)

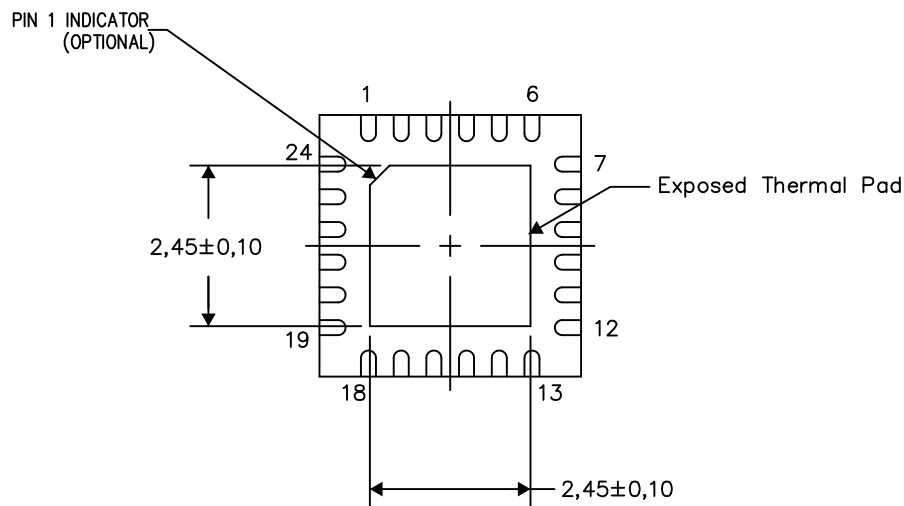
PLASTIC QUAD FLATPACK NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

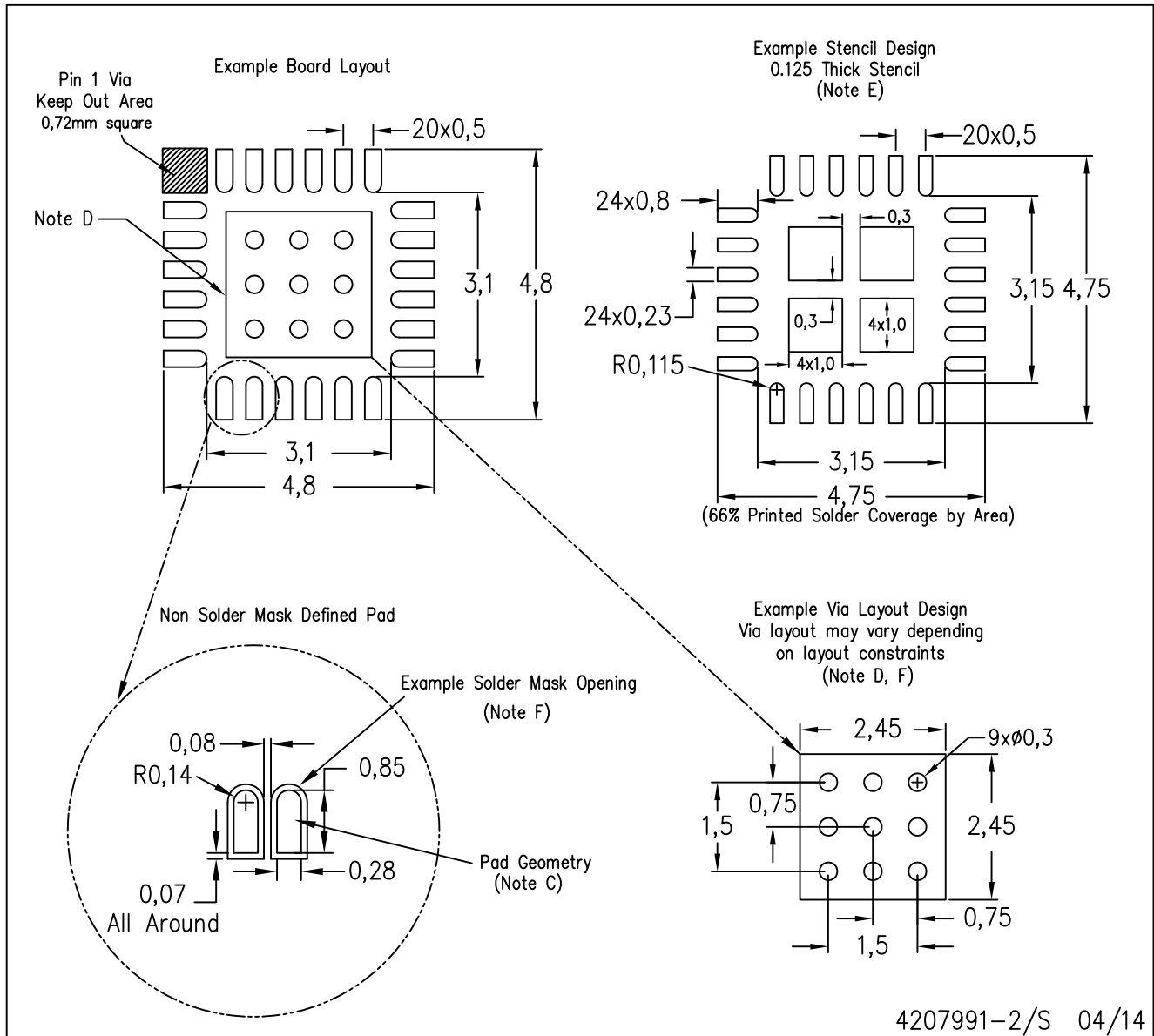
Exposed Thermal Pad Dimensions

4206344-3/AH 08/14

NOTES: A. All linear dimensions are in millimeters

RGE (S-PVQFN-N24)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at [www.ti.com](http://www.ti.com) <<http://www.ti.com>>.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.

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